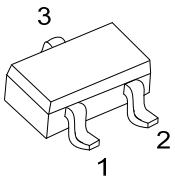
DTA115T

PNP SILICON TRANSISTOR

DIGITAL TRANSISTORS (BUILT- IN BIAS RESISTORS)

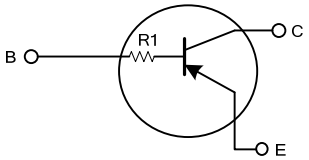


SOT-23
(JEDEC TO-236)

■ FEATURES

* Built-in bias resistors that implies easy ON/OFF applications.
* The bias resistors are thin-film resistors with complete isolation to allow positive input.

■ EQUIVALENT CIRCUIT



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
DTA115TL-AE3-R	DTA115TG-AE3-R	SOT-23	B	E	C	Tape Reel

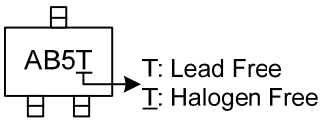
Note: Pin Assignment: B: Base E: Emitter C: Collector

DTA115TG-AE3-R

(1)Packing Type
(2)Package Type
(3)Green Package

(1) R: Tape Reel
(2) AE3: SOT-23
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL SPECIFICATIONS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-50μA	-50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-1mA	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-50μA	-5			V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=-1mA, I_B=-0.1mA			-0.3	V
Collector Cutoff Current	I_{CBO}	V_{CB}=-50V			-0.5	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-4V			-0.5	μA
DC Current Gain	h_{FE}	V_{CE}=-5V, I_C=-1mA	100	250	600	
Input Resistance	R_1		70	100	130	kΩ
Transition Frequency	f_T	V_{CE}=-10V, I_E=5mA,f=100MHz (Note)		250		MHz

Note: Transition frequency of the device